

# EUROPEAN PATENT OFFICE

00177698  
106. B5

## Patent Abstracts of Japan

PUBLICATION NUMBER : 61001060  
PUBLICATION DATE : 07-01-86

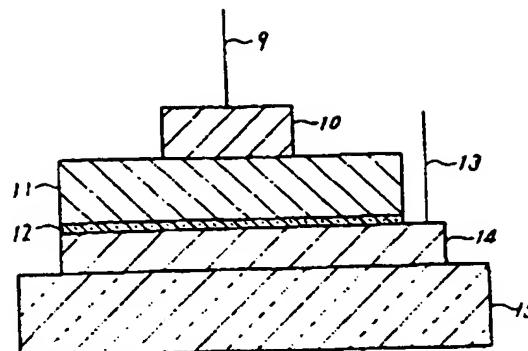
APPLICATION DATE : 13-06-84  
APPLICATION NUMBER : 59124096

APPLICANT : MITSUBISHI ELECTRIC CORP;

INVENTOR : ANDO TORAHICO;

INT.CL. : H01L 29/91 H01L 29/48 H01L 31/04

TITLE : MANUFACTURE OF MIS DIODE



ABSTRACT : PURPOSE: To obtain high and stable performance by forming an insulating organic layer on a metal electrode by electrolytic polymerizing method, forming a semiconductor layer thereon, and further forming a conductive layer to become an electrode thereon.

CONSTITUTION: An Al electrode 14 is formed on a glass substrate 15 as an operating electrode. A poly  $\alpha$ -naphthole layer 12 is precipitated as an insulating organic polymer layer on the electrode to obtain an insulating organic polymer sample. A poly N-methylpyrrole film 11 is precipitated as a  $\pi$ -conjugate polymer layer on the sample, and an Au electrode 10 is formed on the film 11. A MIS diode having high performance and stable performance can be readily formed by the above manufacturing method.

COPYRIGHT: (C)1986,JPO&Japio

BEST AVAILABLE COPY